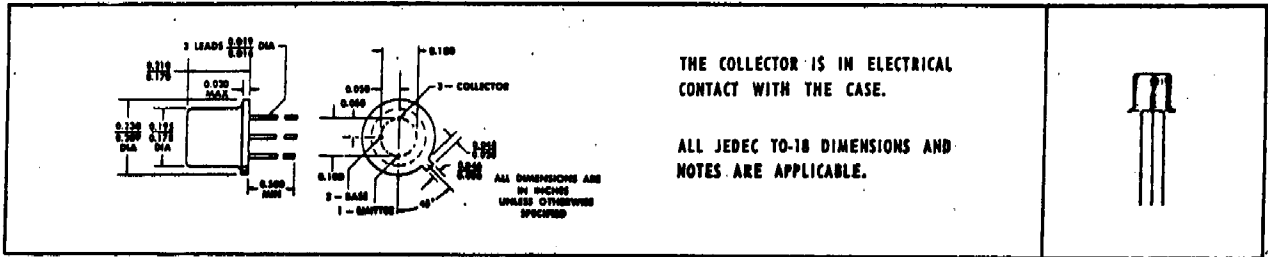


TYPES 2N3033, 2N3034, 2N3035

N-P-N EPITAXIAL MESA SILICON TRANSISTORS

**DESIGNED FOR EXTREMELY-HIGH-SPEED, HIGH-CURRENT
 AVALANCHE-MODE SWITCHING APPLICATIONS**

- Strobe-Pulse Generators
- Square-Wave Pulse Generators
- Memory-Core Drivers

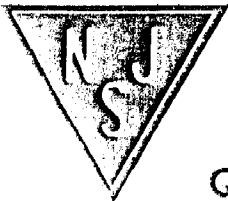


absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Emitter-Base Voltage	4 v
Collector Current, Continuous	200 ma
Collector Current, Peak (See Note 1)	10 a
Total Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 2)	300 mw
Total Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	1.0 w
Storage Temperature Range	-65°C to +200°C

electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N3033		2N3034		2N3035		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
BV_{CBO} Collector-Base Breakdown Voltage	$I_C = 1 \text{ ma}, I_E = 0$	100	160	70	120	50	90	v
BV_{CEB} Collector-Emitter Breakdown Voltage	$I_C = 1 \text{ ma}, R_{BE} = 100 \Omega$	100	150	70	110	50	80	v
BV_{EBO} Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{a}, I_C = 0$	4		4		4		v
I_{CBO} Collector Cutoff Current	$V_{CB} - \text{See Note 4}, I_E = 0$		5		5		5	μa
I_{CBR} Collector Cutoff Current	$V_{CE} - \text{See Note 5}, R_{BE} = 100 \Omega$		5		5		5	μa
	$V_{CE} = 90 \text{ v}, R_{BE} = 100 \Omega, T_A = 125^\circ\text{C}$		50					μa
	$V_{CE} = 60 \text{ v}, R_{BE} = 100 \Omega, T_A = 125^\circ\text{C}$				50			μa
I_{EB0} Emitter Cutoff Current	$V_{EB} = 3 \text{ v}, I_C = 0$		1		1		1	μa
$I_{CES(H)}$ Collector Hold-Off Current	$V_{BE} = 0, (\text{See Note 6})$	2.0		2.0		2.0		ma
$I_{CER(H)}$ Collector Hold-Off Current	$R_{BE} = 100 \Omega, (\text{See Note 6})$	1.5		1.5		1.5		ma
V_{BE} Base-Emitter Voltage	$I_E = 20 \text{ ma}, I_C = 100 \text{ ma}$		1.5		1.5		1.5	v
$V_{CE(sat)}$ Collector-Emitter Saturation Voltage	$I_E = 20 \text{ ma}, I_C = 100 \text{ ma}$		1.0		1.0		1.0	v
C_{ob} Common-Base Open-Circuit Output Capacitance	$V_{CB} = 10 \text{ v}, I_E = 0, f = 140 \text{ kc}$		6		6		6	pf
C_{ib} Common-Base Open-Circuit Input Capacitance	$V_{EB} = 1 \text{ v}, I_C = 0, f = 140 \text{ kc}$		10		10		10	pf



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

- NOTES: 1. This value applies for $PW \leq 25$ nsec, Duty Cycle $\leq 0.05\%$.
2. Derate linearly to 175°C free-air temperature at the rate of 2.0 mw/C°.
3. Derate linearly to 175°C case temperature at the rate of 6.67 mw/C°.
4. This parameter is measured at a collector-base voltage 15 v below the actual BV_{CBO} at $I_C = 1$ ma, $I_B = 0$.
5. This parameter is measured at a collector-emitter voltage 15 v below the actual BV_{CEB} at $I_C = 1$ ma, $R_{BE} = 100 \Omega$.
6. Collector Hold-Off Current is defined as that value of collector cutoff current above which the reverse voltage-current characteristic exhibits negative resistance. These parameters are measured by a sweep method using a transistor curve tracer.

switching characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS	2N3033		2N3034		2N3035		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_d Delay Time	See Figure 1	3		3		3		nsec
t_r Rise Time		2		2		2		nsec
V_o Output Pulse Amplitude		45		30		20		v